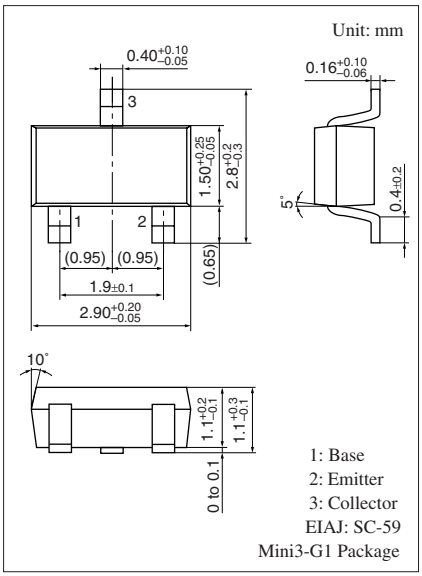
UNR221x Series (UN221x Series)

Silicon NPN epitaxial planar transistor

For digital circuits



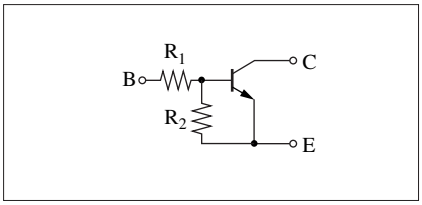
■ Features

- Costs can be reduced through downsizing of the equipment and reduction of the number of parts.
- Mini type package allowing easy automatic insertion through tape packing and magazine packing

■ Resistance by Part Number

		Marking Symbol	(R_1)	(R_2)
• UNR2210	(UN2210)	8L	47 kΩ	—
• UNR2211	(UN2211)	8A	10 kΩ	10 kΩ
• UNR2212	(UN2212)	8B	22 kΩ	22 kΩ
• UNR2213	(UN2213)	8C	47 kΩ	47 kΩ
• UNR2214	(UN2214)	8D	10 kΩ	47 kΩ
• UNR2215	(UN2215)	8E	10 kΩ	—
• UNR2216	(UN2216)	8F	4.7 kΩ	—
• UNR2217	(UN2217)	8H	22 kΩ	—
• UNR2218	(UN2218)	8I	0.51 kΩ	5.1 kΩ
• UNR2219	(UN2219)	8K	1 kΩ	10 kΩ
• UNR221D	(UN221D)	8M	47 kΩ	10 kΩ
• UNR221E	(UN221E)	8N	47 kΩ	22 kΩ
• UNR221F	(UN221F)	8O	4.7 kΩ	10 kΩ
• UNR221K	(UN221K)	8P	10 kΩ	4.7 kΩ
• UNR221L	(UN221L)	8Q	4.7 kΩ	4.7 kΩ
• UNR221M	(UN221M)	EL	2.2 kΩ	47 kΩ
• UNR221N	(UN221N)	EX	4.7 kΩ	47 kΩ
• UNR221T	(UN221T)	EZ	22 kΩ	47 kΩ
• UNR221V	(UN221V)	FD	2.2 kΩ	2.2 kΩ
• UNR221Z	(UN221Z)	FF	4.7 kΩ	22 kΩ

Internal Connection



■ Absolute Maximum Ratings $T_a = 25°C$

Parameter	Symbol	Rating	Unit
Collector-base voltage (Emitter open)	V_{CBO}	50	V
Collector-emitter voltage (Base open)	V_{CEO}	50	V
Collector current	I_C	100	mA
Total power dissipation	P_T	200	mW
Junction temperature	T_j	150	°C
Storage temperature	T_{stg}	−55 to +150	°C

Note) The part numbers in the parenthesis show conventional part number.

■ Electrical Characteristics $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Collector-base voltage (Emitter open)		V_{CBO}	$I_C = 10\ \mu A$, $I_E = 0$	50			V
Collector-emitter voltage (Base open)		V_{CEO}	$I_C = 2$ mA, $I_B = 0$	50			V
Collector-base cutoff current (Emitter open)		I_{CBO}	$V_{CB} = 50$ V, $I_E = 0$			0.1	μA
Collector-emitter cutoff current (Base open)		I_{CEO}	$V_{CE} = 50$ V, $I_B = 0$			0.5	μA
Emitter-base cutoff current (Collector open)	UNR2210/2215/2216/2217	I_{EBO}	$V_{EB} = -6$ V, $I_C = 0$			0.01	mA
	UNR2213					0.1	
	UNR2212/2214/221D/221E/221M/221N/221T					0.2	
	UNR221Z					0.4	
	UNR2211					0.5	
	UNR221F/221K					1.0	
	UNR2219					1.5	
	UNR2218/221L/221V					2.0	
Forward current transfer ratio	UNR221V	h_{FE}	$V_{CE} = 10$ V, $I_C = 5$ mA	6		20	—
	UNR2218/221K/221L			20			
	UNR2219/221D/221F			30			
	UNR2211			35			
	UNR2212/221E			60			
	UNR221Z			60		200	
	UNR2213/2214/221M			80			
	UNR221N/221T			80		400	
	UNR2210*/2215*/2216*/2217*			160		460	
Collector-emitter saturation voltage		$V_{CE(sat)}$	$I_C = 10$ mA, $I_B = 0.3$ mA			0.25	V
	UNR221V		$I_C = 10$ mA, $I_B = 1.5$ mA				
Output voltage high-level		V_{OH}	$V_{CC} = 5$ V, $V_B = 0.5$ V, $R_L = 1$ kΩ	4.9			V
Output voltage low-level		V_{OL}	$V_{CC} = 5$ V, $V_B = 2.5$ V, $R_L = 1$ kΩ			0.2	V
	UNR2213/221K		$V_{CC} = 5$ V, $V_B = 3.5$ V, $R_L = 1$ kΩ				
	UNR221D		$V_{CC} = 5$ V, $V_B = 10$ V, $R_L = 1$ kΩ				
	UNR221E		$V_{CC} = 5$ V, $V_B = 6$ V, $R_L = 1$ kΩ				
Transition frequency		f_T	$V_{CB} = 10$ V, $I_E = -2$ mA, f = 200 MHz		150		MHz
Input resistance	UNR2218	R_1		−30%	0.51	+30%	kΩ
	UNR2219				1.0		
	UNR221M/211V				2.2		
	UNR2216/221F/221L/221N/221Z				4.7		
	UNR2211/2214/2215/221K				10		
	UNR2212/2217/221T				22		
	UNR2210/2213/221D/221E				47		

Note) 1. Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

2. *: Rank classification

Rank	Q	R	S	No-rank
h_{FE}	160 to 260	210 to 340	290 to 460	160 to 460

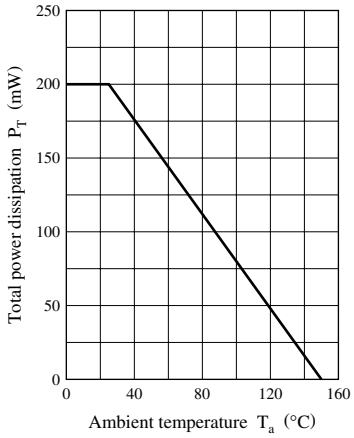
■ Electrical Characteristics (continued) $T_a = 25°C \pm 3°C$

Parameter		Symbol	Conditions	Min	Typ	Max	Unit
Resistance ratio	UNR221M	R_1/R_2			0.047		—
	UNR221N				0.1		
	UNR2218/2219			0.08	0.10	0.12	
	UNR221Z				0.21		
	UNR2214			0.17	0.21	0.25	
	UNR221T				0.47		
	UNR221F			0.37	0.47	0.57	
	UNR221V				1.0		
	UNR2211/2212/2213/221L			0.8	1.0	1.2	
	UNR221K			1.70	2.13	2.60	
	UNR221E			1.70	2.14	2.60	
	UNR221D			3.7	4.7	5.7	

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 measuring methods for transistors.

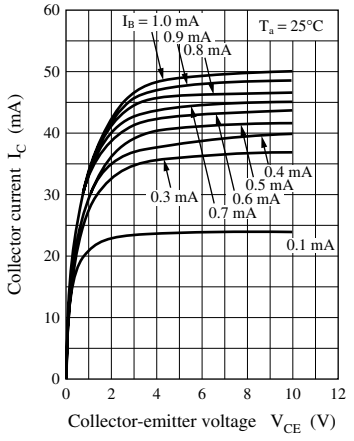
Common characteristics chart

P_T — T_a

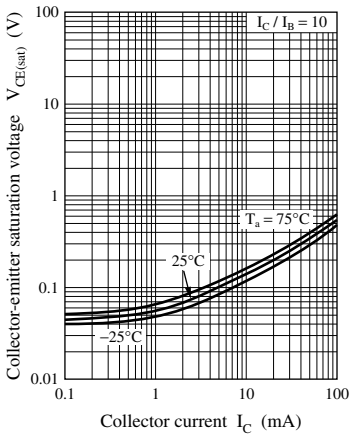


Characteristics charts of UNR2210

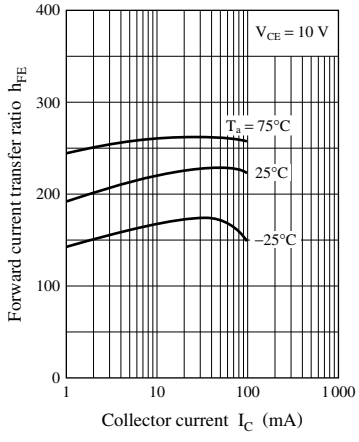
I_C — V_{CE}



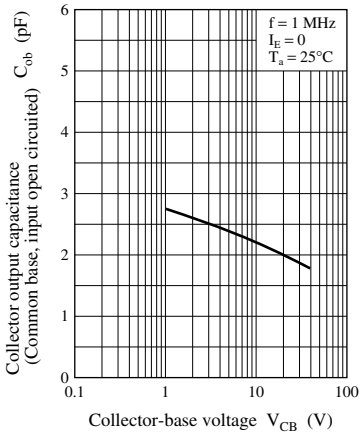
$V_{CE(sat)}$ — I_C



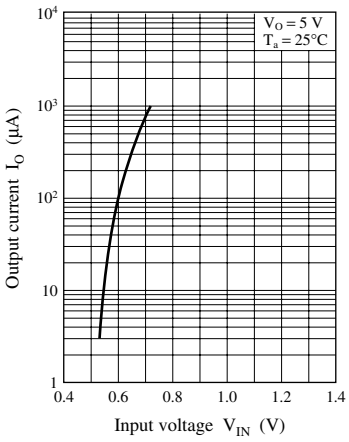
h_{FE} — I_C



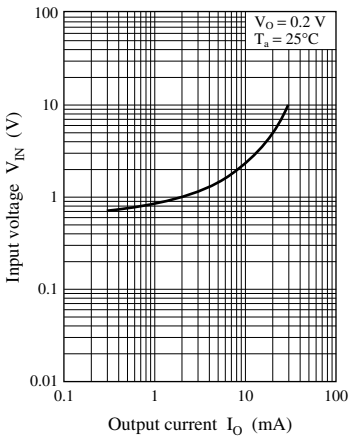
C_{ob} — V_{CB}



I_O — V_{IN}

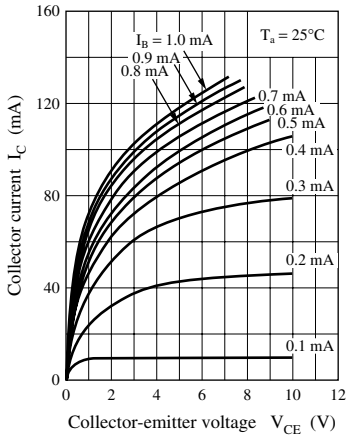


V_{IN} — I_O

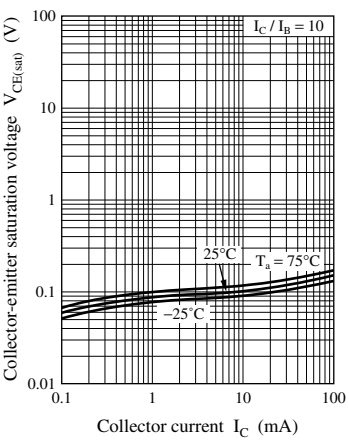


Characteristics charts of UNR2211

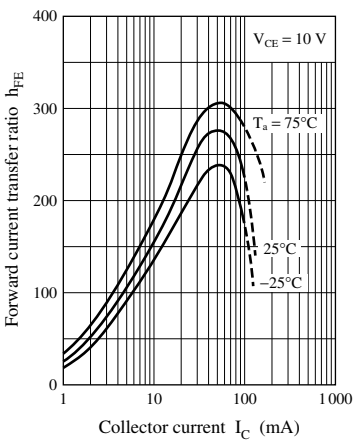
I_C — V_{CE}



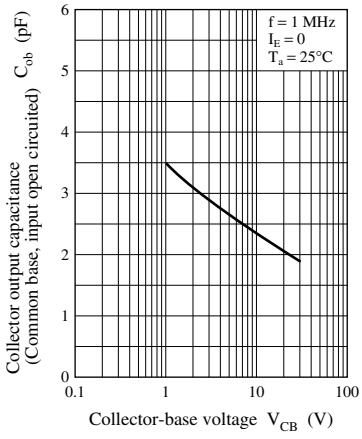
$V_{CE(sat)}$ — I_C



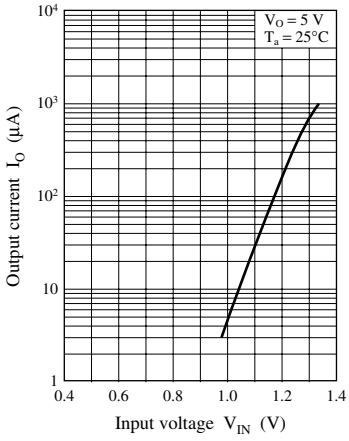
h_{FE} — I_C



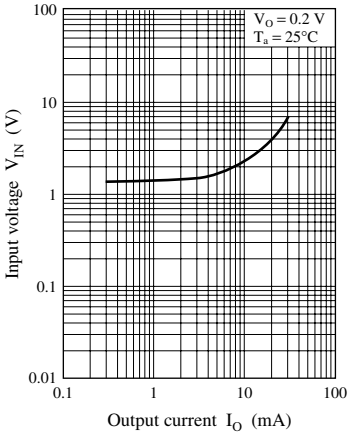
C_{ob} — V_{CB}



I_O — V_{IN}

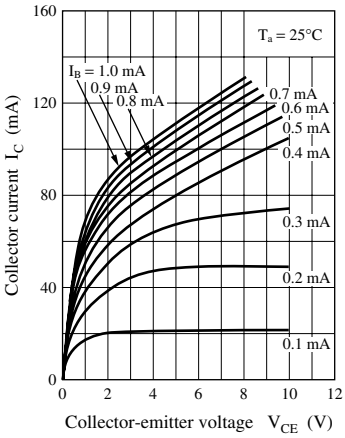


V_{IN} — I_O

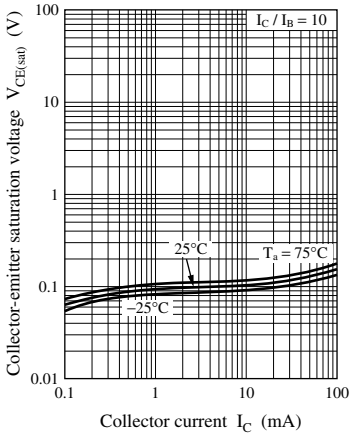


Characteristics charts of UNR2212

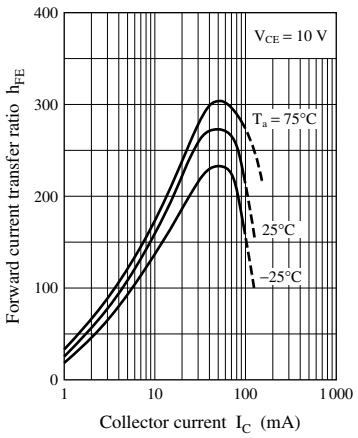
I_C — V_{CE}



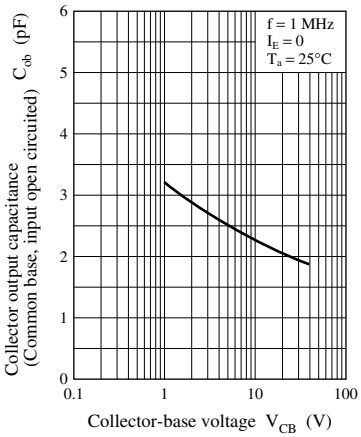
$V_{CE(sat)}$ — I_C



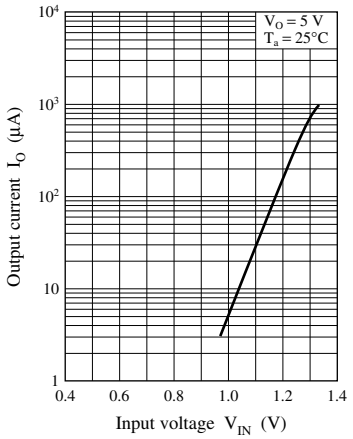
h_{FE} — I_C



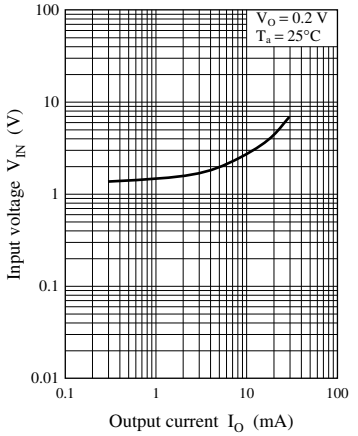
C_{ob} — V_{CB}



I_O — V_{IN}

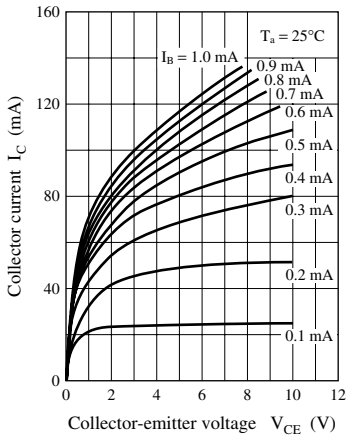


V_{IN} — I_O

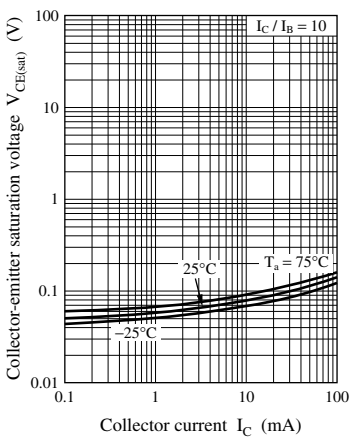


Characteristics charts of UNR2213

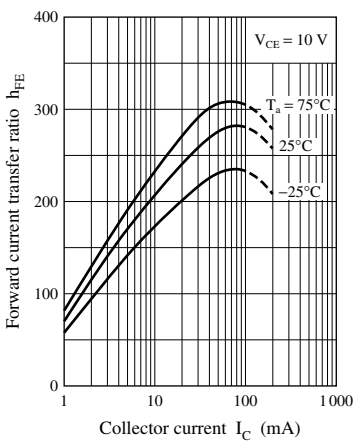
I_C — V_{CE}



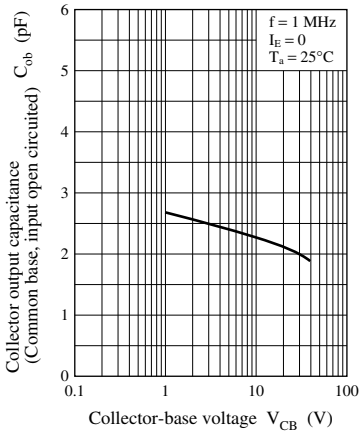
$V_{CE(sat)}$ — I_C



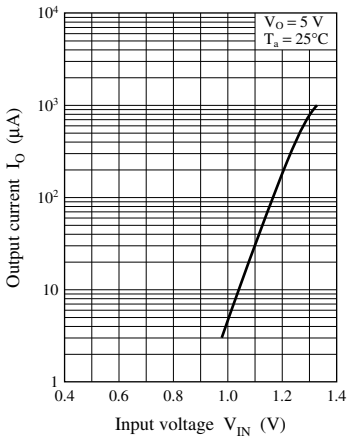
h_{FE} — I_C



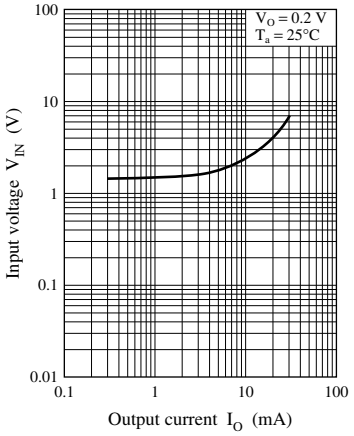
C_{ob} — V_{CB}



I_O — V_{IN}

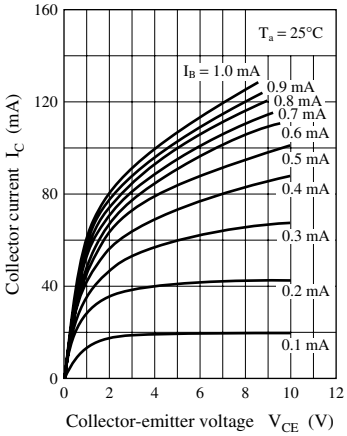


V_{IN} — I_O

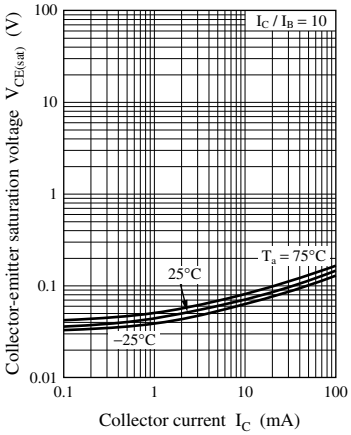


Characteristics charts of UNR2214

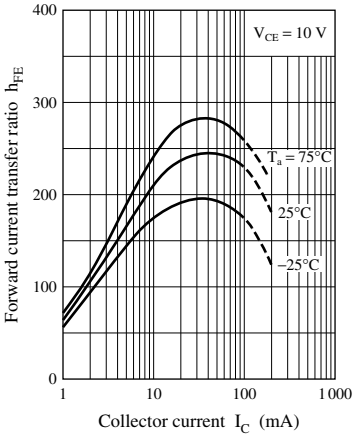
I_C — V_{CE}



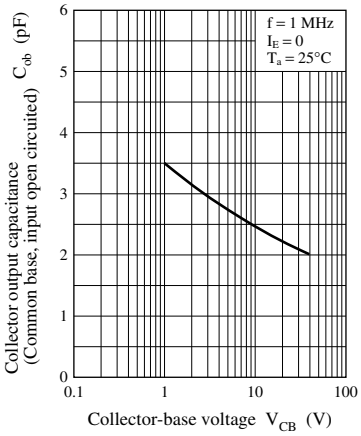
$V_{CE(sat)}$ — I_C



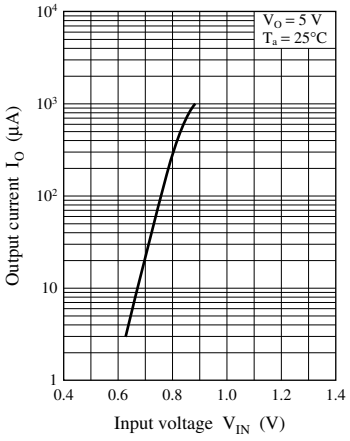
h_{FE} — I_C



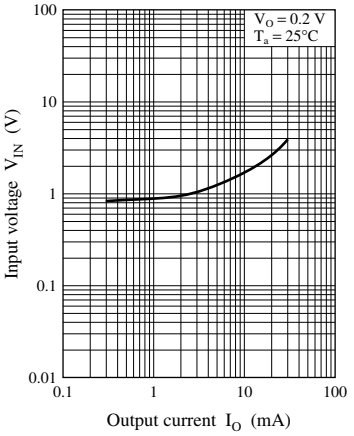
C_{ob} — V_{CB}



I_O — V_{IN}

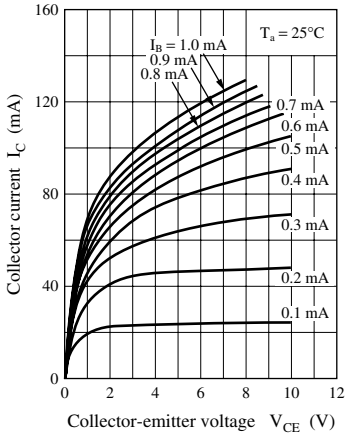


V_{IN} — I_O

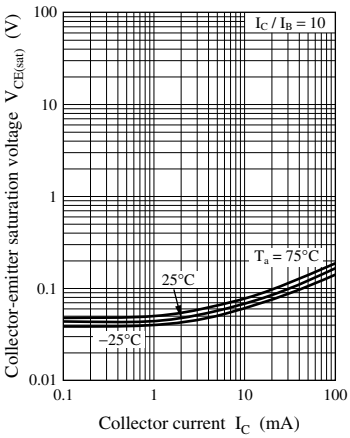


Characteristics charts of UNR2215

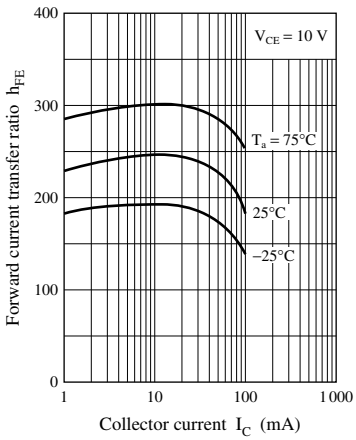
I_C — V_{CE}



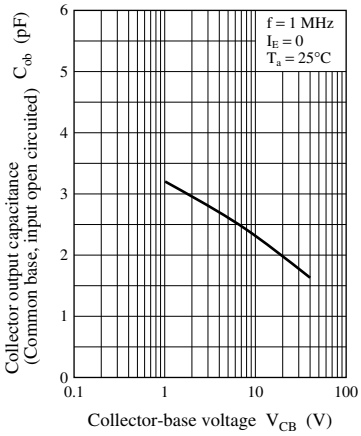
$V_{CE(sat)}$ — I_C



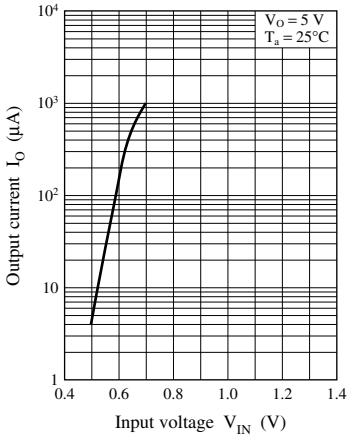
h_{FE} — I_C



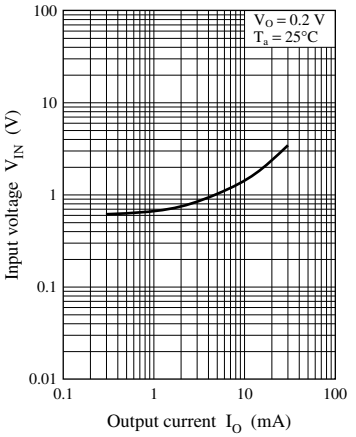
C_{ob} — V_{CB}



I_O — V_{IN}

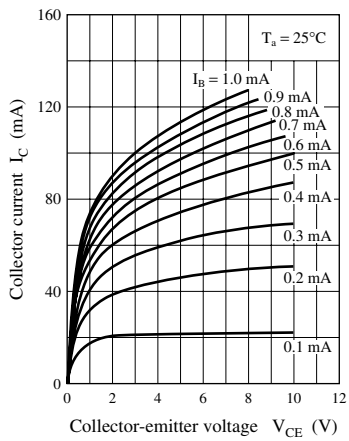


V_{IN} — I_O

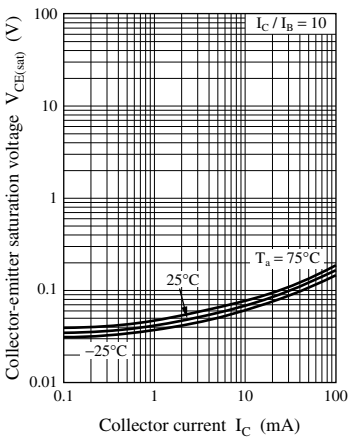


Characteristics charts of UNR2216

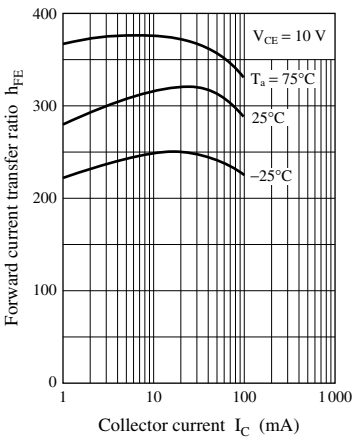
I_C — V_{CE}



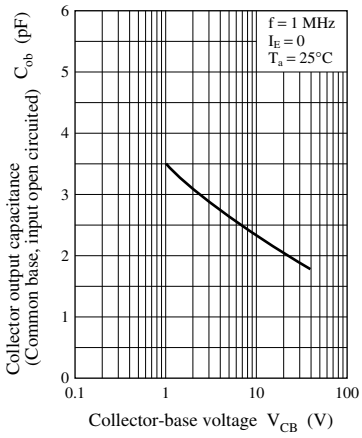
$V_{CE(sat)}$ — I_C



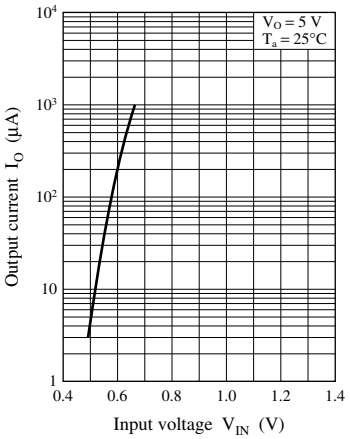
h_{FE} — I_C



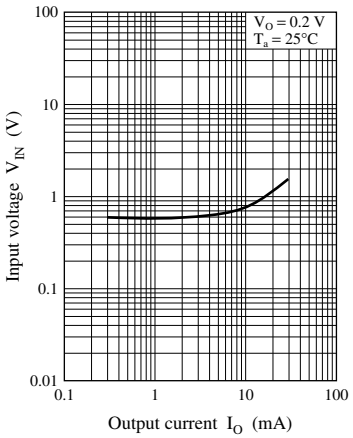
C_{ob} — V_{CB}



I_O — V_{IN}

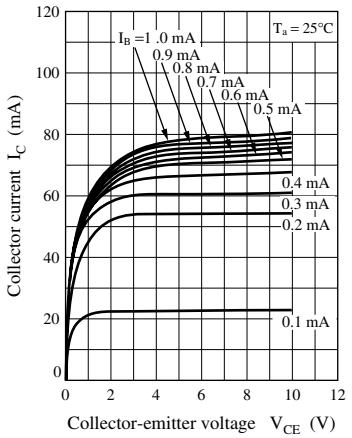


V_{IN} — I_O

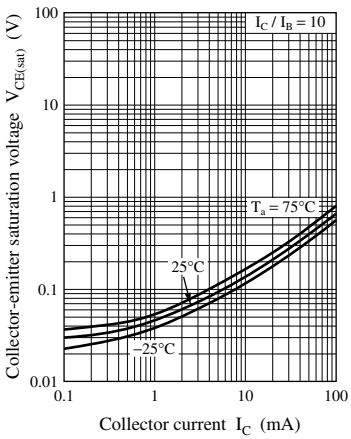


Characteristics charts of UNR2217

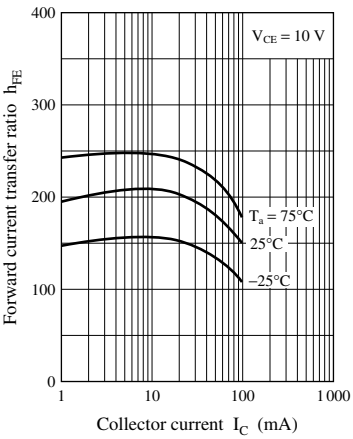
I_C — V_{CE}



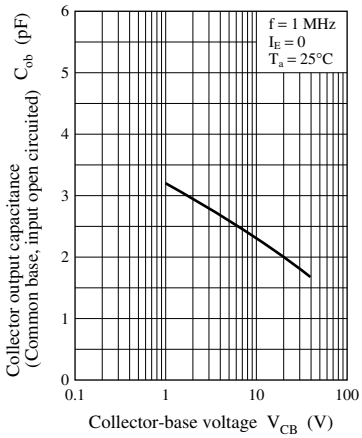
$V_{CE(sat)}$ — I_C



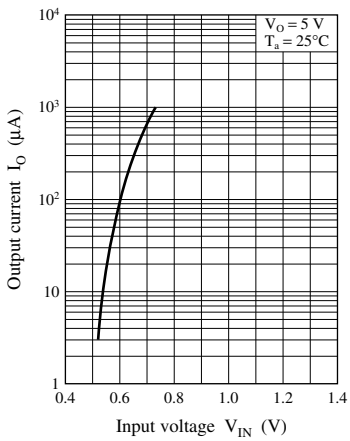
h_{FE} — I_C



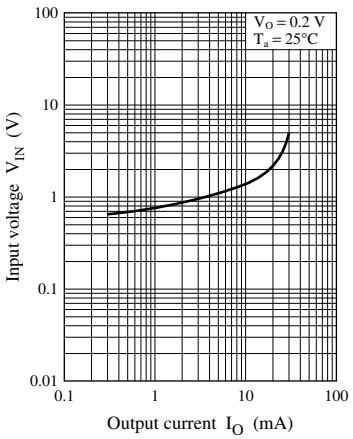
C_{ob} — V_{CB}



I_O — V_{IN}

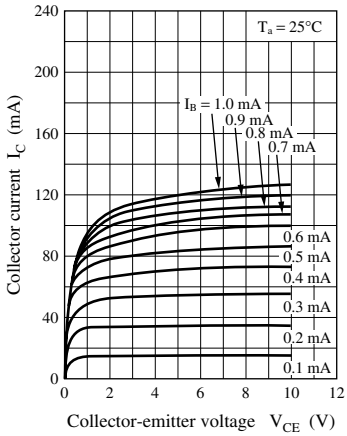


V_{IN} — I_O

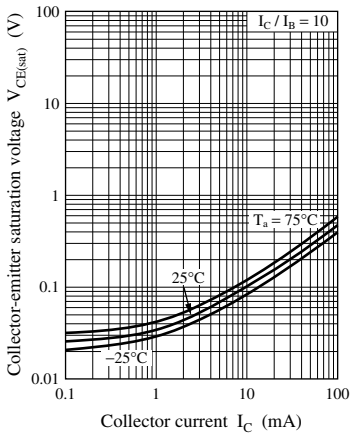


Characteristics charts of UNR2218

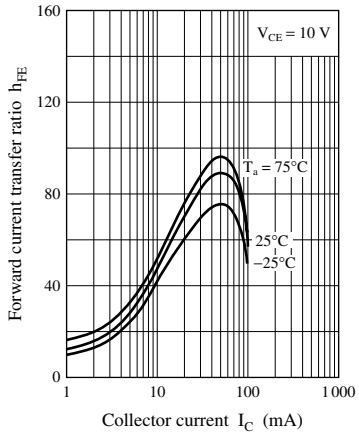
I_C — V_{CE}



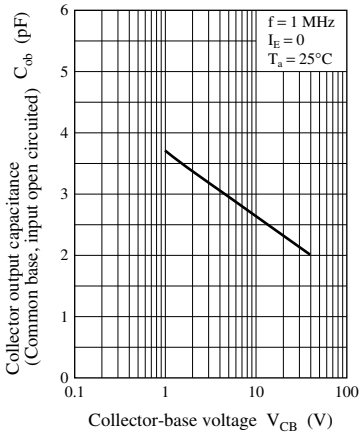
$V_{CE(sat)}$ — I_C



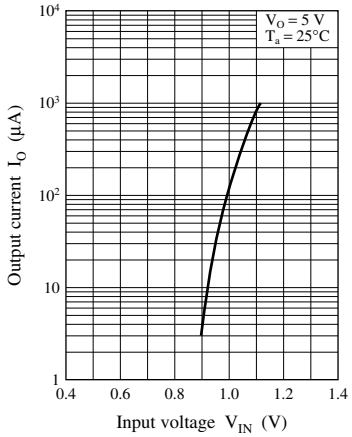
h_{FE} — I_C



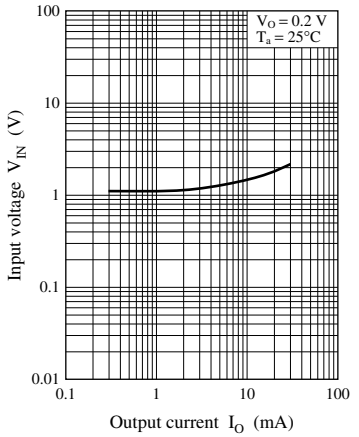
C_{ob} — V_{CB}



I_O — V_{IN}

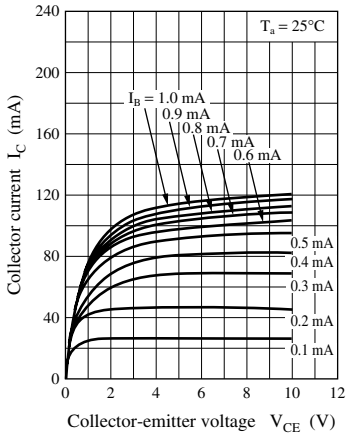


V_{IN} — I_O

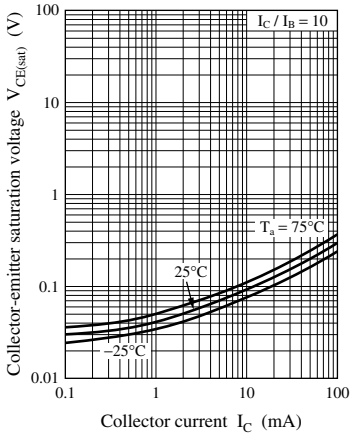


Characteristics charts of UNR2219

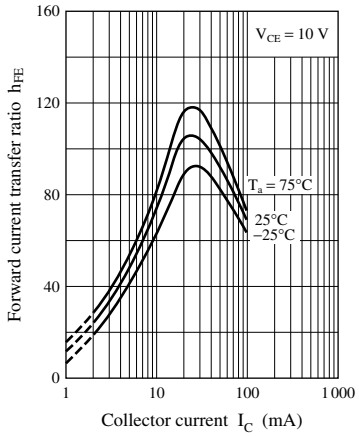
I_C — V_{CE}



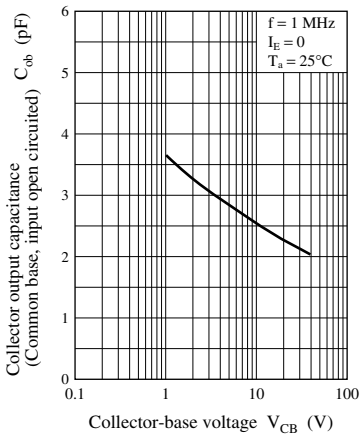
$V_{CE(sat)}$ — I_C



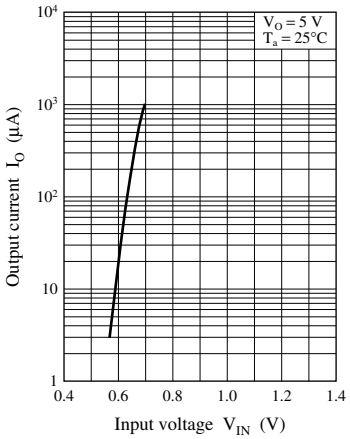
h_{FE} — I_C



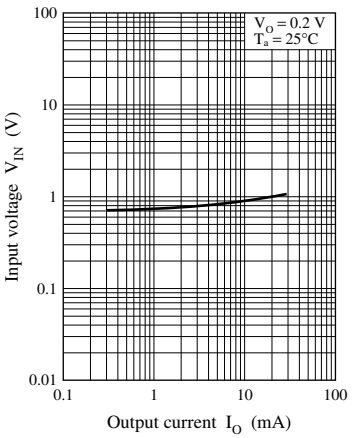
C_{ob} — V_{CB}



I_O — V_{IN}

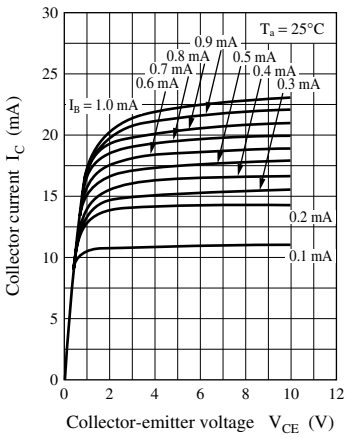


V_{IN} — I_O

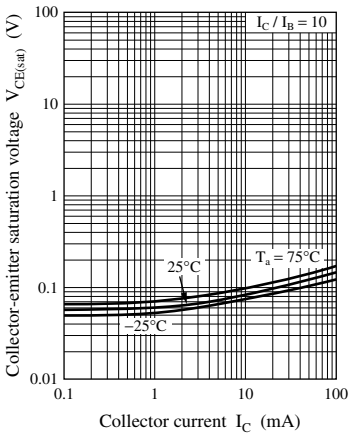


Characteristics charts of UNR221D

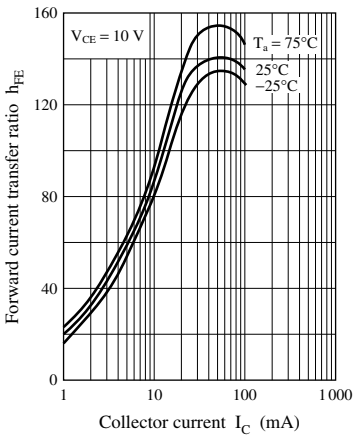
I_C — V_{CE}



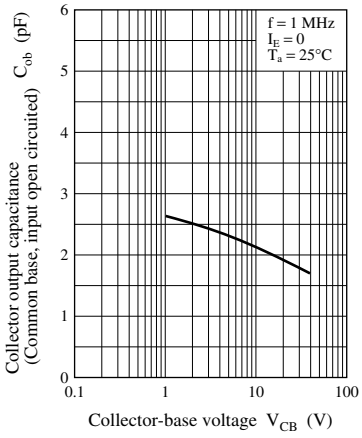
$V_{CE(sat)}$ — I_C



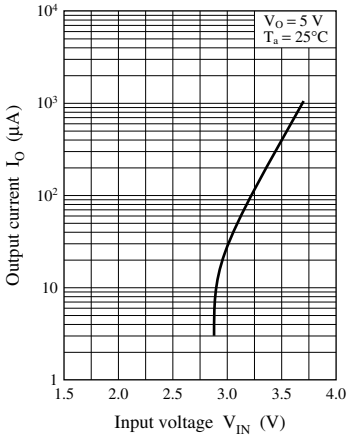
h_{FE} — I_C



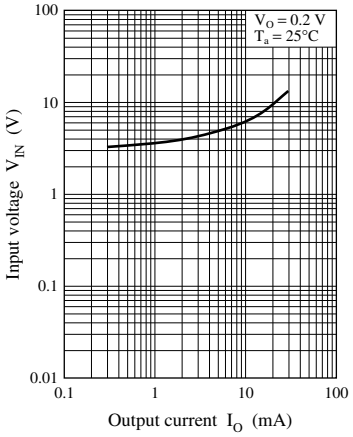
C_{ob} — V_{CB}



I_O — V_{IN}

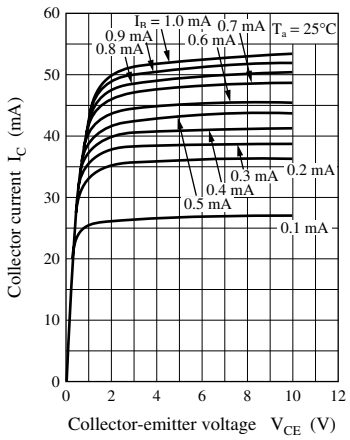


V_{IN} — I_O

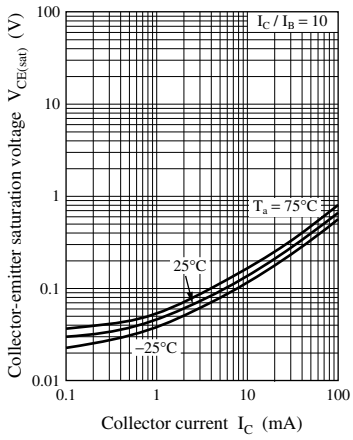


Characteristics charts of UNR221E

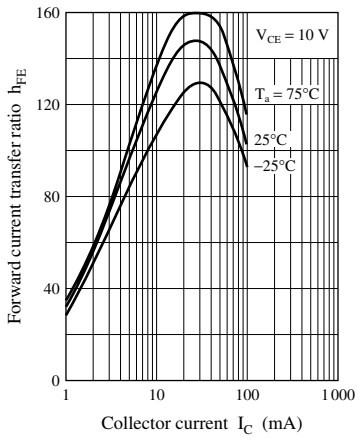
I_C — V_{CE}



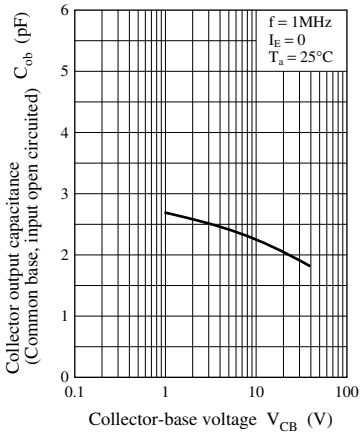
$V_{CE(sat)}$ — I_C



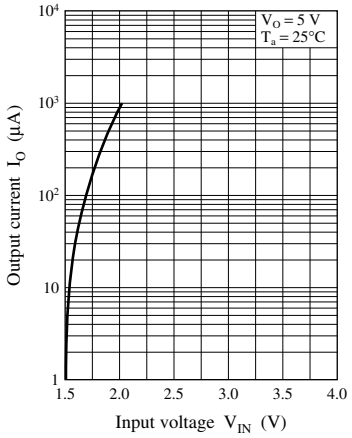
h_{FE} — I_C



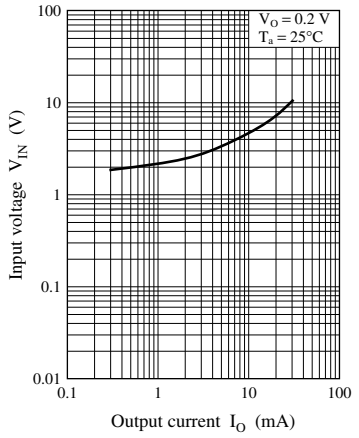
C_{ob} — V_{CB}



I_O — V_{IN}

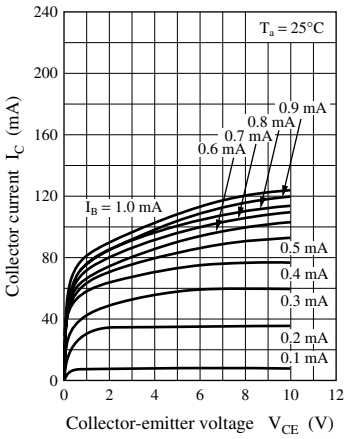


V_{IN} — I_O

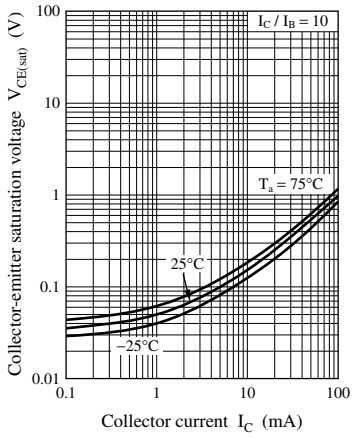


Characteristics charts of UNR221F

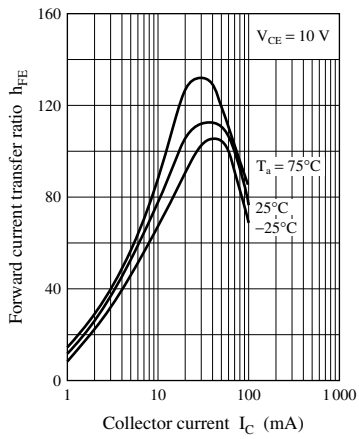
I_C — V_{CE}



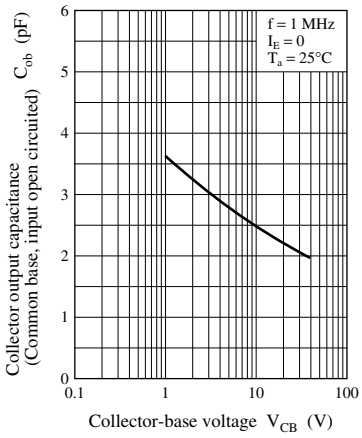
$V_{CE(sat)}$ — I_C



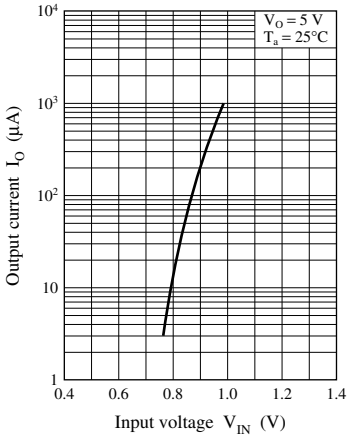
h_{FE} — I_C



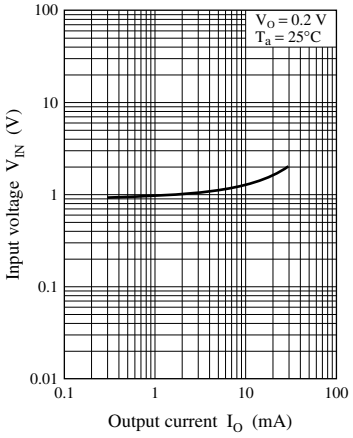
C_{ob} — V_{CB}



I_O — V_{IN}

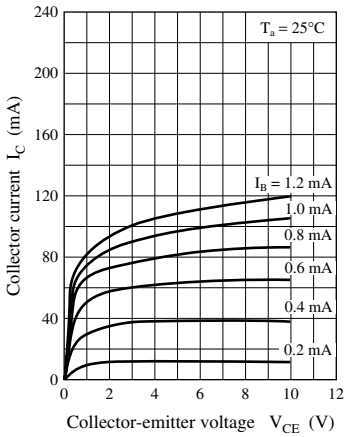


V_{IN} — I_O

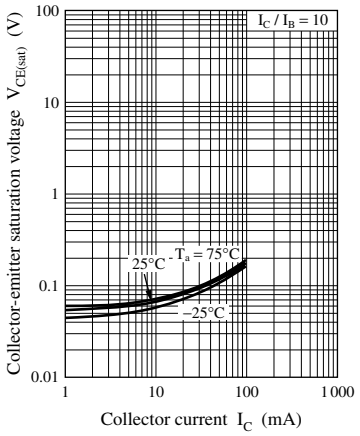


Characteristics charts of UNR221K

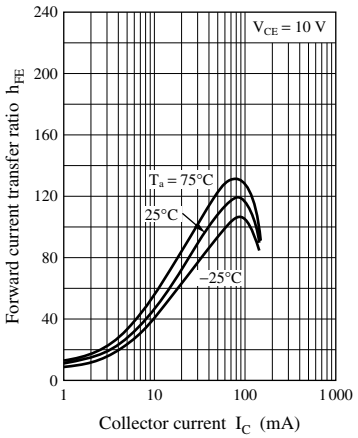
I_C — V_{CE}



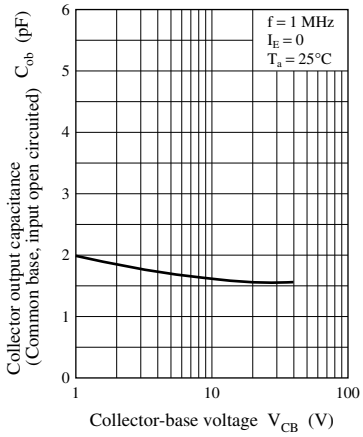
$V_{CE(sat)}$ — I_C



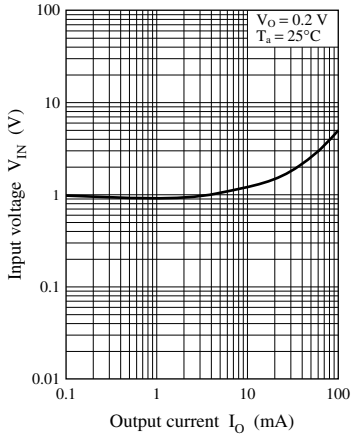
h_{FE} — I_C



C_{ob} — V_{CB}

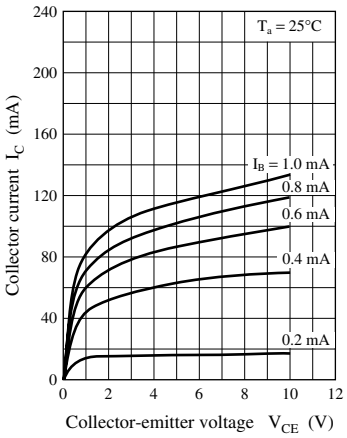


V_{IN} — I_O

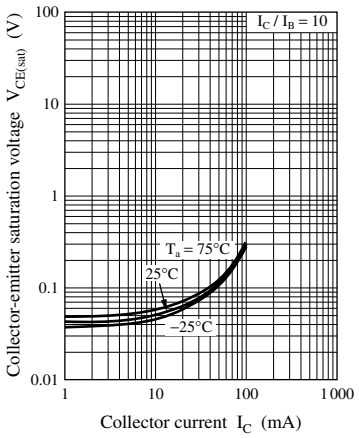


Characteristics charts of UNR221L

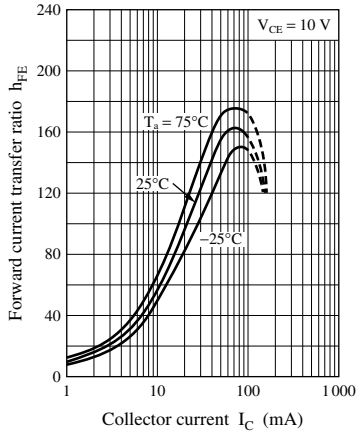
I_C — V_{CE}



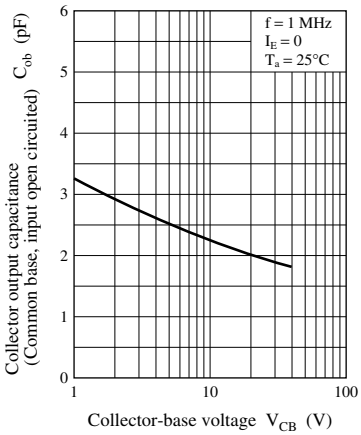
$V_{CE(sat)}$ — I_C



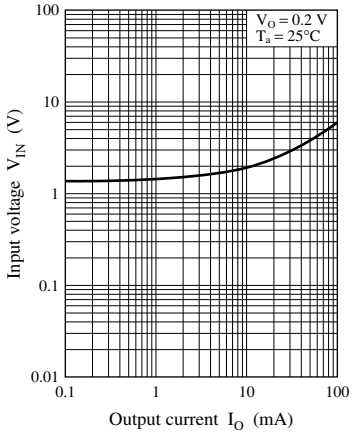
h_{FE} — I_C



C_{ob} — V_{CB}

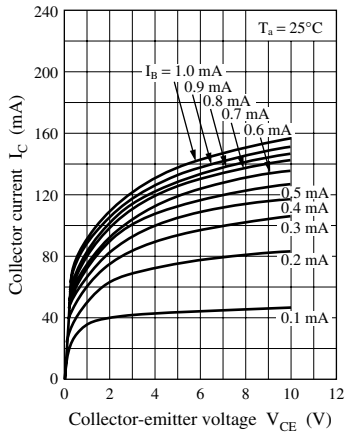


V_{IN} — I_O

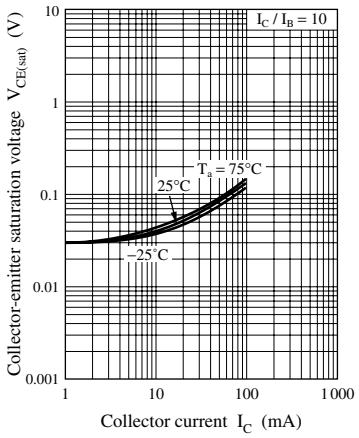


Characteristics charts of UNR221M

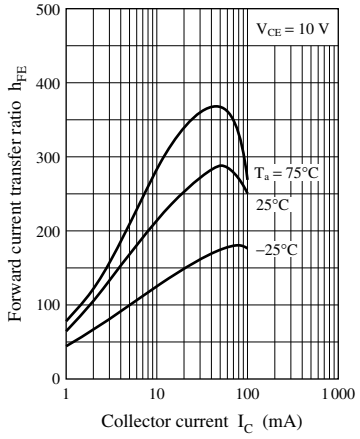
I_C — V_{CE}



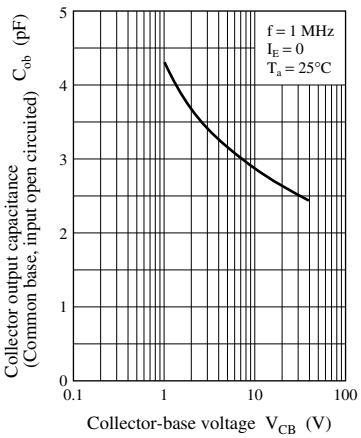
$V_{CE(sat)}$ — I_C



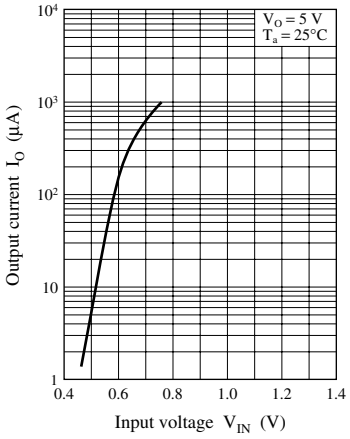
h_{FE} — I_C



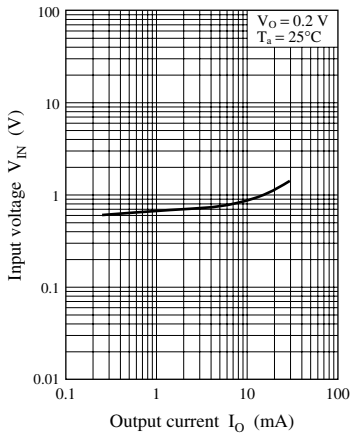
C_{ob} — V_{CB}



I_O — V_{IN}

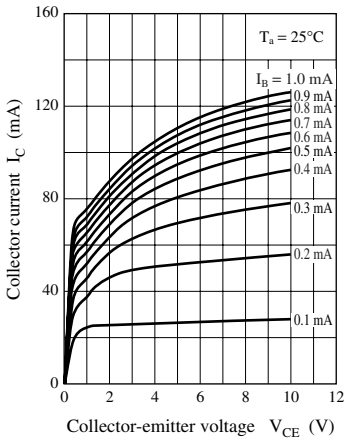


V_{IN} — I_O

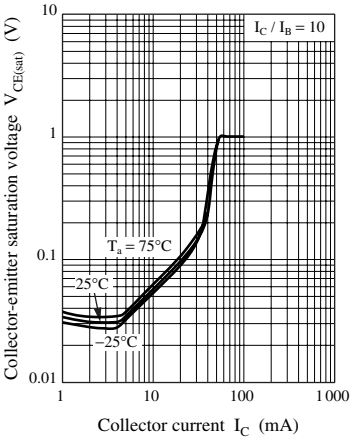


Characteristics charts of UNR221N

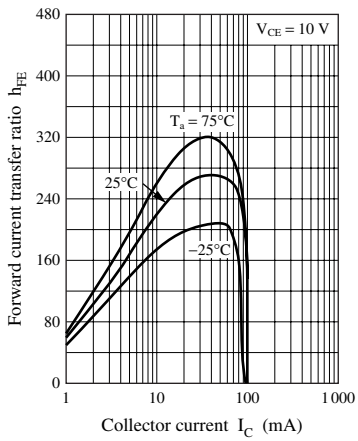
I_C — V_{CE}



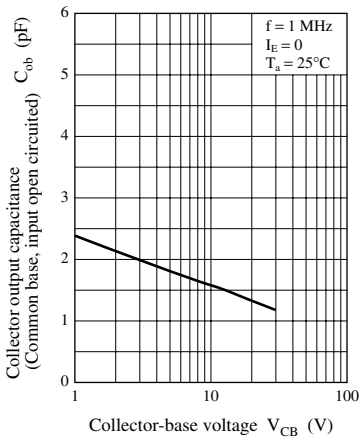
$V_{CE(sat)}$ — I_C



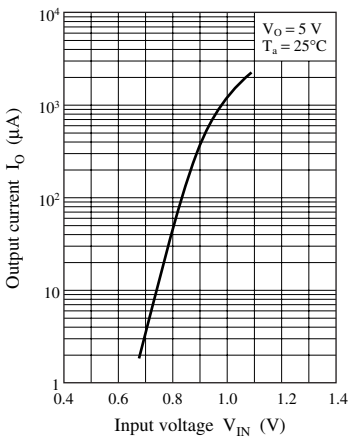
h_{FE} — I_C



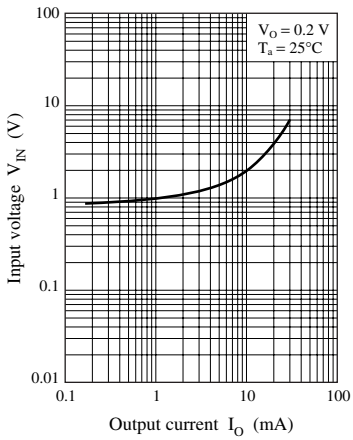
C_{ob} — V_{CB}



I_O — V_{IN}

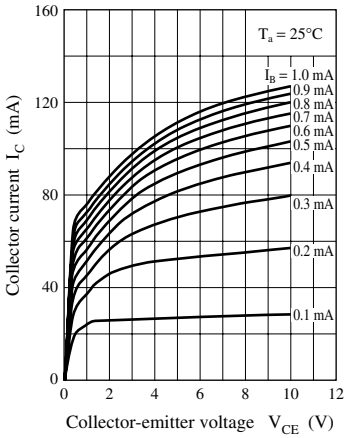


V_{IN} — I_O

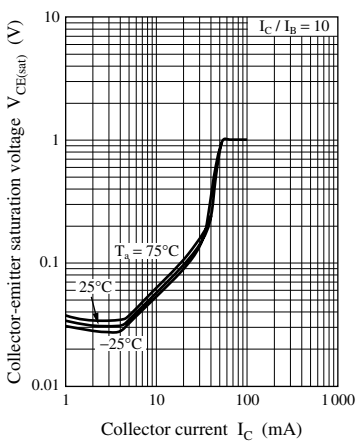


Characteristics charts of UNR221T

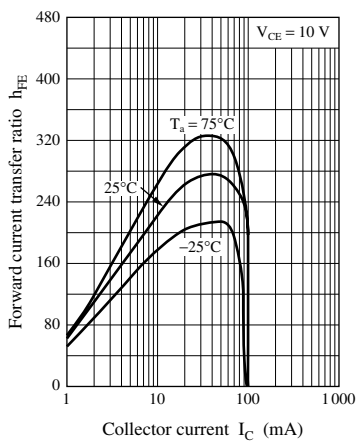
I_C — V_{CE}



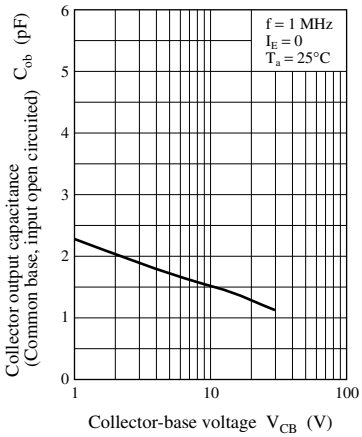
$V_{CE(sat)}$ — I_C



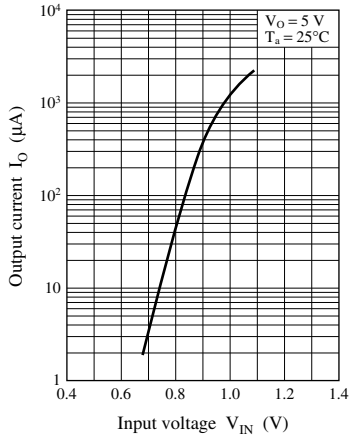
h_{FE} — I_C



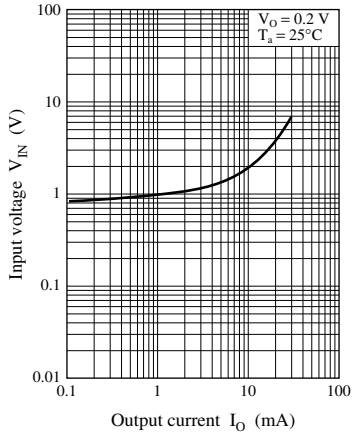
I_O — V_{IN}



I_O — V_{IN}

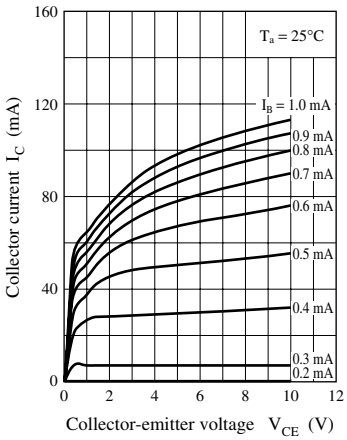


V_{IN} — I_O

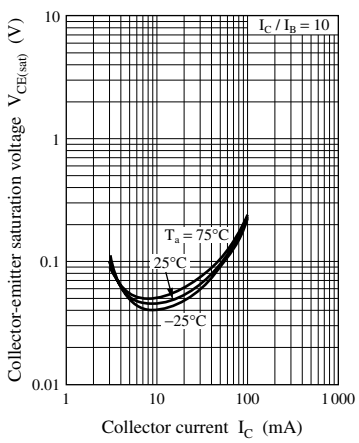


Characteristics charts of UNR221V

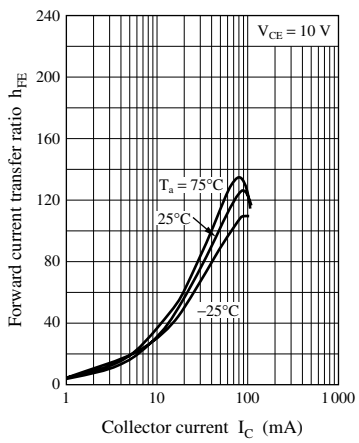
I_C — V_{CE}



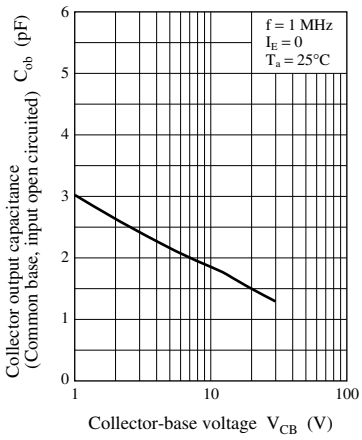
$V_{CE(sat)}$ — I_C



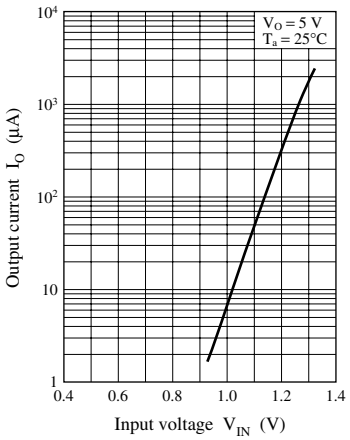
h_{FE} — I_C



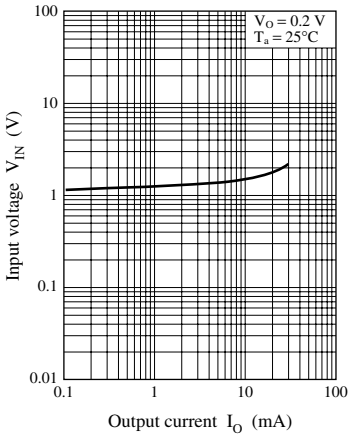
C_{ob} — V_{CB}



I_O — V_{IN}

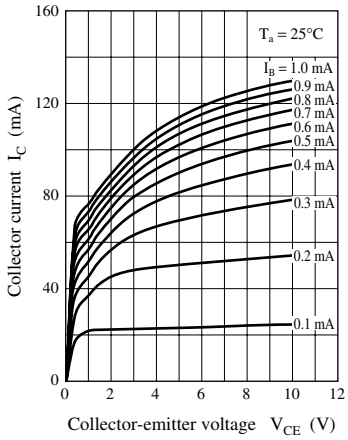


V_{IN} — I_O

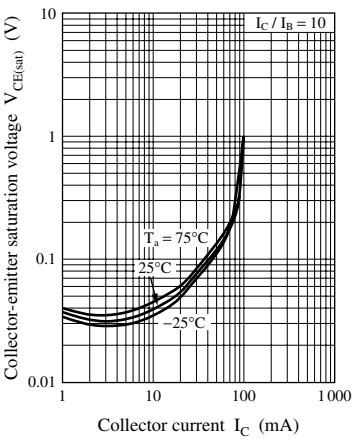


Characteristics charts of UNR221Z

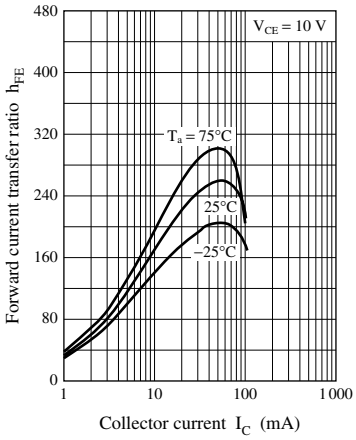
I_C — V_{CE}



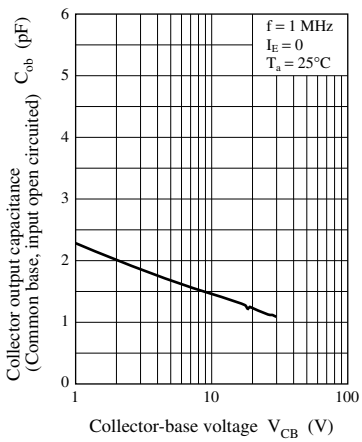
$V_{CE(sat)}$ — I_C



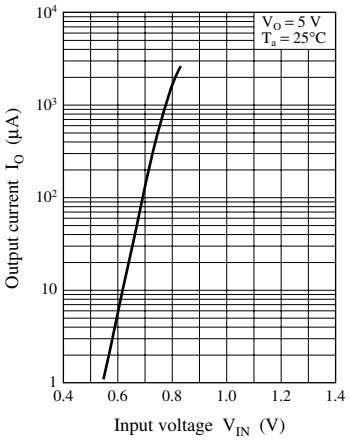
h_{FE} — I_C



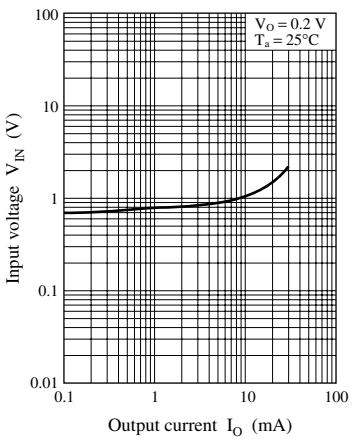
C_{ob} — V_{CB}



I_O — V_{IN}



V_{IN} — I_O



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